

NEIFELD IP LAW REFERENCE FORM LIST OF REFERENCES CITED BY THE APPLICANT (Rev: 5/14/2003)	NEIFELD REF: OSEM-DB3	APPLICATION NO: 09/636,484
	FIRST NAMED INVENTOR: Walter David BRADDOCK	
	FILING DATE: 8/10/2000	GROUP ART UNIT: 2811

LISTING OF UNITED STATES PATENTS

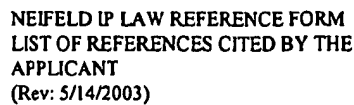
EXAMINER INITIALS	REFERENCE NUMBER (U SERIES)	PATENT NUMBER	ISSUE DATE	NAME OF PATENTEE OR APPLICANT	PAGE/LINE AND FIGURE/ELEMENT OF RELEVANT MATERIAL AND/OR IDENTIFICATION OF PRIORITY APPLICATION IN WHICH REFERENCE IS CITED
OHIC	U-1	3,950,273	4-1976	Jones	
	U-2	4,404,265	9-1983	Manasevit	
	U-3	4,410,902	10-1983	Malik	
	U-4	4,416,952	11-1983	Nishizawa et al.	Of Record
	U-5	4,561,915	12-1985	Mito	Of Record
	U-6	4,624,901	11-1986	Glass	
	U-7	4,671,777	6-1987	van Esdonk et al.	
	U-8	4,685,193	8-1987	Faria et al.	
	U-9	4,745,082	5-1988	Kwok	Of Record
	U-10	4,802,180	1-1989	Brandt, Jr. et al.	Of Record
	U-11	4,843,450	6-1989	Kirchner et al.	Of Record
	U-12	4,859,253	8-1989	Buchanan et al.	Of Record
	U-13	4,935,789	6-1990	Calviello	Of Record
	U-14	4,970,060	11-1990	Belt et al.	
	U-15	5,055,445	10-1991	Belt et al.	
	U-16	5,124,762	6-1992	Childs et al.	Of Record
	U-17	5,170,407	12-1992	Schubert et al.	
	U-18	5,270,798	12-1993	Pao et al.	
	U-19	5,323,053	6-1994	Luryi et al.	
	U-20	5,386,137	1-1995	Dell et al.	
	U-21	5,425,043	6-1995	Holonyak et al.	
	U-22	5,451,548	9-1995	Hunt et al.	Of Record
	U-23	5,491,712	2-1996	Lin et al.	
	U-24	5,550,089	8-1996	Dutta et al.	Of Record
Date:	10-26-04	Examiner's Signature: <i>Kunstner</i>			



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DHA	U-25	5,597,768	1-1997	Passlack et al.	Of Record
	U-26	5,640,751	6-1997	Faria	
	U-27	5,665,658	9-1997	Passlack	Of Record
	U-28	5,693,565	12-1997	Camilletti et al.	Of Record
	U-29	5,729,563	3-1998	Wang et al.	
	U-30	5,767,388	6-1998	Fletcher et al.	Of Record
	U-31	5,805,624	9-1998	Yang et al.	
	U-32	5,821,171	10-1998	Hong et al.	Of Record
	U-33	5,838,708	11-1998	Lin et al.	
	U-34	5,896,408	4-1999	Corzine et al.	
	U-35	5,930,611	7-1999	Okamoto	Of Record
	U-36	5,945,718	8-1999	Passlack et al.	Of Record
	U-37	5,953,362	9-1999	Pamulapati et al.	
	U-38	6,006,582	12-1999	Bhandari et al.	Of Record
	U-39	6,028,693	2-2000	Fork et al.	
	U-40	6,030,453	2-2000	Passlack et al.	Of Record
	U-41	6,045,611	4-2000	Ishii et al.	
	U-42	6,069,908	5-2000	Yuen et al.	
	U-43	6,071,780	6-2000	Okamoto et al.	Of Record
	U-44	6,094,295	7-2000	Passlack et al.	Of Record
	U-45	6,114,079	9-2000	Christian et al.	
	U-46	6,150,677	11-2000	Tanaka et al.	Of Record
	U-47	6,207,976	3-2001	Takahashi et al.	Of Record
	U-48	6,252,896	6-2001	Tan et al.	
Date: 10-26-04			Examiner's Signature:		



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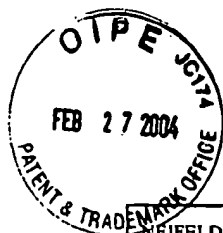
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LISTING OF NON PATENT LITERATURE

EXAMINER INITIALS	REFERENCE NUMBER (L Series)	PUBLICATION DATE	INCLUDE IN SEQUENCE: Name of first author (in CAPITAL LETTERS), Title in quotation marks, name of publication, date of publication, page numbers, publisher, city of publication, and country of publication	ENGLISH LANGUAGE TRANSLATION ATTACHED? (YES OR NO) AND/OR OR IDENTIFICATION OF PRIORITY APPLICATION IN WHICH REFERENCE IS CITED
hnu	L-1	1994	"1995-1996 Alfa AESAR Catalog," 1994, page 1244, Johnson Matthey Catalog Company, Inc., Ward Hill, MA, US.	
	L-2	6-2001	VURGATMAN et al., "Band Parameters for III-V Semiconductors and Their Alloys," J. Appl. Phys. PP 5816-5875 (June 1, 2001).	Of Record
	L-3	2003	"Gallium Oxide on Gallium Arsenide: Atomic Structure, Materials, and Devices," Chapter 12, either published or scheduled for publication in "Gallium Oxide on Gallium Arsenide: Atomic Structure, Materials, and Devices," in III-IV Semiconductor Heterostructures: Physics and Devices, edited by W.Z. Cai, Transworld Research Publisher, Kerala, India (2003).	Of Record
	L-4	7-1996	PASSLACK et al., "Thermodynamic and photochemical stability of low interface static density Ga ₂ O ₃ -GaAs structures fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Vol 69, No 3, pps 302-304, 15 July 1996.	Of Record
	L-5	6-1997	PASSLACK et al., "Recombination velocity at oxide-GaAs interfaces fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Volume 68, Number 25, pages 3605-3607, 17 June 1997.	Of Record
	L-6	2-1996	PASSLACK et al., "Quasistatic and high frequency capacitance-voltage characterization of Ga ₂ O ₃ -GaAs structures fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Volume 68, Number 8, pages 1099-1101, 19 February 1996.	Of Record
	L-7	8-1997	UEDA et al., "Anisotropy of electrical and optical properties in D-Ga ₂ O ₃ single crystals", Applied Physics Letters, Volume 71, Number 7, Pages 933-935, 18 August 1997.	Of Record
	L-8	6-1997	UEDA et al., "Synthesis and control of conductivity of ultraviolet transmitting D-Ga ₂ O ₃ single crystals", Applied Physics Letters, Volume 70, Number 26, pages 3561-3563, 30 June 1997.	Of Record
	L-9	2-2000	KHAN et al., "AlGaIn/GaN Metal Oxide Semiconductor Heterostructure Field Effect Transistor", IEEE Electron Device Letters, Volume 21, Number 2, pages 63-65, Feb. 2000.	

Date: 10-26-04	Examiner's Signature: <i>[Signature]</i>
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NEIFELD IP LAW REFERENCE FORM LIST OF REFERENCES CITED BY THE APPLICANT (Rev: 5/14/2003)	NEIFELD REF: OSEM-DB3	APPLICATION NO: 09/636,484
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<i>DNK</i>	U-1	3,950,273	4-1976	Jones	Of Record
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	U-9	4,745,082	5-1988	Kwok	Of Record
	U-10	4,802,180	1-1989	Brandt, Jr. et al.	Of Record
	U-11	4,843,450	6-1989	Kirchner et al.	Of Record
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	U-18	5,270,798	12-1993	Pao et al.	Of Record
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	U-20	5,386,137	1-1995	Beit et al.	Of Record
	U-21	5,425,043	6-1995	Holonyak et al.	Of Record
	U-22	5,451,548	9-1995	Hunt et al.	Of Record
	U-23	5,491,712	2-1996	Lin et al.	Of Record
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<i>DM</i>	U-25	5,597,768	1-1997	Passlack et al.	Of Record
	U-26	5,640,751	6-1997	Faria	Of Record
	U-27	5,665,658	9-1997	Passlack	Of Record
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	U-29	5,729,563	3-1998	Wang et al.	Of Record
	U-30	5,767,388	6-1998	Fletcher et al.	Of Record
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	U-37	5,953,362	9-1999	Pannulapati et al.	Of Record
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	U-43	6,071,780	6-2000	Okamoto et al.	Of Record
	U-44	6,094,295	7-2000	Passlack et al.	Of Record
	U-45	6,114,079	9-2000	Christian et al.	Of Record
	U-46	6,150,677	11-2000	Tanaka et al.	Of Record
	U-47	6,207,976	3-2001	Takahashi et al.	Of Record
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LISTING OF FOREIGN AND INTERNATIONAL PATENT DOCUMENTS

EXAMINER INITIALS	REFERENCE NUMBER (F SERIES)	PUBLICATION NUMBER	PUBLICATION DATE	COUNTRY OR REGION	PAGE/LINE AND FIGURE/ELEMENT OF RELEVANT MATERIAL	ENGLISH LANGUAGE TRANSLATION ATTACHED? (YES OR NO) AND/OR IDENTIFICATION OF PRIORITY APPLICATION IN WHICH REFERENCE IS CITED						
<i>nmh</i>	F+	JP 8085873 A	4-1998	Japan	Yoshizawa et al.	yes Of Record						
							Date: 10-26-04		Examiner's Signature: <i>[Signature]</i>			



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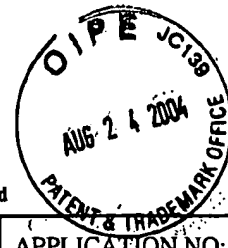
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DNUL	E-1	1994	"1995-1996 Alfa AESAR Catalog," 1994, page 1244, Johnson Matthey Catalog Company, Inc., Ward Hill, MA, US.	Of Record
	E-2	6-2001	VURGATMAN et al., "Band Parameters for III-V Semiconductors and Their Alloys," J. Appl. Phys. PP-5816-5875 (June 1, 2001).	Of Record
	E-3	2003	"Gallium Oxide on Gallium Arsenide: Atomic Structure, Materials, and Devices," Chapter 12, either published or scheduled for publication in "Gallium Oxide on Gallium Arsenide: Atomic Structure, Materials, and Devices," in III-IV Semiconductor Heterostructures: Physics and Devices, edited by W.Z. Cai, Transworld Research Publisher, Kerala, India (2003).	Of Record
	E-4	7-1996	PASSLACK et al., "Thermodynamic and photochemical stability of low interface state density Ga2O3-GaAs structures fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Vol 69, No 3, pps 302-304, 15 July 1996.	Of Record
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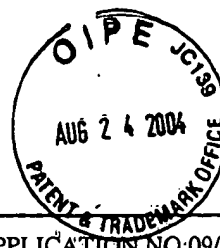
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LISTING OF NON PATENT LITERATURE - O Series

EXAMINER INITIALS	REFERENCE NUMBER (O Series)	PUBLICATION DATE	INCLUDE IN SEQUENCE: Name of first author (in CAPITAL LETTERS), Title in quotation marks, name of publication, date of publication, page numbers, publisher, city of publication, and country of publication	ENGLISH LANGUAGE TRANSLATION ATTACHED? (YES OR NO) AND/OR OR IDENTIFICATION OF PRIORITY APPLICATION IN WHICH REFERENCE IS CITED
<i>DHL</i>	O-1	4/28/1965	BECKE et al., "Gallium Arsenide Mos Transistors," Solid-State Electronics, 1965, Vol. 8, pp. 813-822, Great Britain.	No
<i>hnl</i>	O-2	12/3/1995	PASSLACK et al., "C-V and G-V Characterization of In-Situ Fabricated Ga2O3-GaAs Interfaces for Inversion/Accumulati on Device and Surface Passivation Applications," Solid- State Electronics, 1996, Vol. 39, No. 8, pp. 1133-1136, Great Britain	No
<i>hm</i>	O-3	2/19/1996	PASSLACK et al., "Quasistatic and High Frequency Capacitance - Voltage Characterization of Ga2O3-GaAs Structures Fabricated by in Situ Molecular Beam Epitaxy," Appl. Phys. Lett., Feb. 19, 1996, pp. 1099-1101.	No
Date: <i>10-26-04</i>		Examiner's Signature: <i>Kong</i>		

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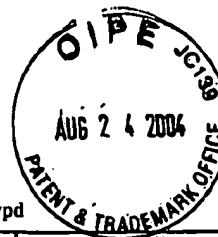
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<i>DHL</i>	O-4	1996	PASSLACK et al., "GaAs Surface Passivation Using in- Situ Oxide Deposition," Applied Surface Science, 1996, pp. 441-447.	No
<i>DHL</i>	O-5	6/1995	PASSLACK et al., "Infrared Microscopy Studies on High- Power InGaAs- GaAs-InGaP Lasers with Ga2O3 Facet Coatings," IEEE Journal of Selected Topics in Quantum Electronics, Vol. 1, No. 2, June 1995, pp. 110-115.	No
<i>nm</i>	O-6	12/15/1995	PASSLACK et al., "Capacitance - Voltage and Current - Voltage Characterization of AlxGa1As - GaAs Structures," J. Appl. Phys., Vol. 78, No. 12, December 15, 1995, pp. 7091-7098	No
Date: <i>10-26-04</i>		Examiner's Signature: <i>Kangshu</i>		

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LISTING OF NON PATENT LITERATURE - O Series (Continued)

<i>PHL</i>	O-7	1997	HONG et al., "Novel Ga ₂ O ₃ (Gd ₂ O ₃) Passivation Techniques to Produce Low Dit Oxide - GaAs Interfaces," Journal of Crystal Growth, 1997, pp. 422-427.	No
<i>PHL</i>	O-8	5/1/1996	HONG et al., "Low Interface State Density Oxide-GaAs Structures Fabricated by in Situ Molecular Beam Epitaxy," J. Vac. Sci. Technol. B., Vol. 14, No. 3, May/Jun 1996, pp. 2297-2300.	No
<i>PHL</i>	O-9	2/1/1997	PASSLACK et al., "Low Dit, Thermodynamically Stable Ga ₂ O ₃ -GaAs Interfaces: Fabrication, Characterization, and Modeling," IEEE Transactions on Electron Devices, Vol. 44, No. 2, February 1997, pp. 214-225.	No
Date: <i>10-26-04</i>		Examiner's Signature: <i>[Signature]</i>		